

INFORMATION DISCLOSURE STATEMENT

Atty Docket:
Serial No.:
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Group: *282*

SE1645PD (50042)

Not Yet Assigned

ZENG

Herewith

09/844,347
04/27/01

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09/844347

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U.S. PATENT DOCUMENTS

Examiner Initials		Document Number	Date	Name	Class	Sub Class	Filing Date
<i>[Signature]</i>	AA	5,567,634	10/22/96	Hébert et al.	437	41	X
<i>[Signature]</i>	AB	5,665,619	9/9/97	Kwan et al.	438	270	
<i>[Signature]</i>	AC	6,121,089	9/19/00	Zeng et al.	438	268	
	AD						X
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						
	AL						

FOREIGN PATENT DOCUMENTS

		Document Number	Date	Country	Class	Sub Class	Translation
	AM						X
	AN						
	AO						
	AP						

OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)

<i>[Signature]</i>	AQ	Zeng, <i>An Improved Power MOSFET Using a Novel Split Well Structure</i> , Harris Corporation, Semiconductor Section, Technical Publication, 4 pages					
<i>[Signature]</i>	AR	Zeng et al., <i>An Ultra Dense Trench-Gated Power MOSFET Technology Using a Self-Aligned Process</i> , Intersil Corporation, Technical Publication, 4 pages					
	AS						

EXAMINER:

DATE CONSIDERED:

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.